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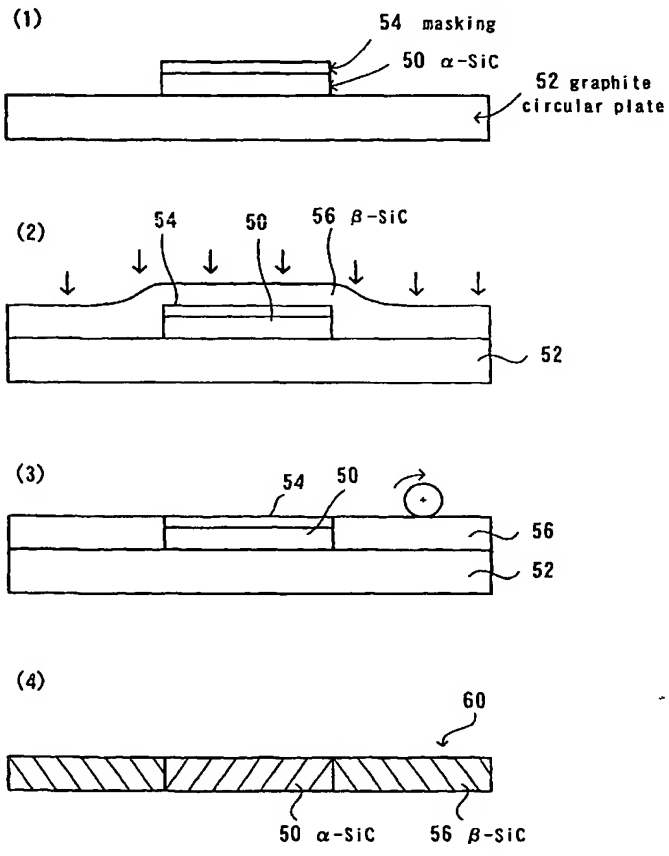
(54) Title: LARGE-DIAMETER SIC WAFER AND MANUFACTURING METHOD THEREOF



(57) Abstract: From the viewpoint of manufacturing an SiC semiconductor device economically, a present Si device manufacturing line is utilized to make it possible to handle a small-diameter SiC wafer. Polycrystal SiC is grown from at least one surface side of a small-diameter a-SiC single crystal wafer so as to be in a size of an outer diameter corresponding to a handling device of an existing semiconductor manufacturing line, and thereafter the polycrystal SiC on the surface of the α-SiC single crystal wafer is ground to manufacture an increased-diameter SiC of a double structure in which the polycrystal SiC is grown around an outer circumference of the small-diameter α-SiC single crystal wafer.

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